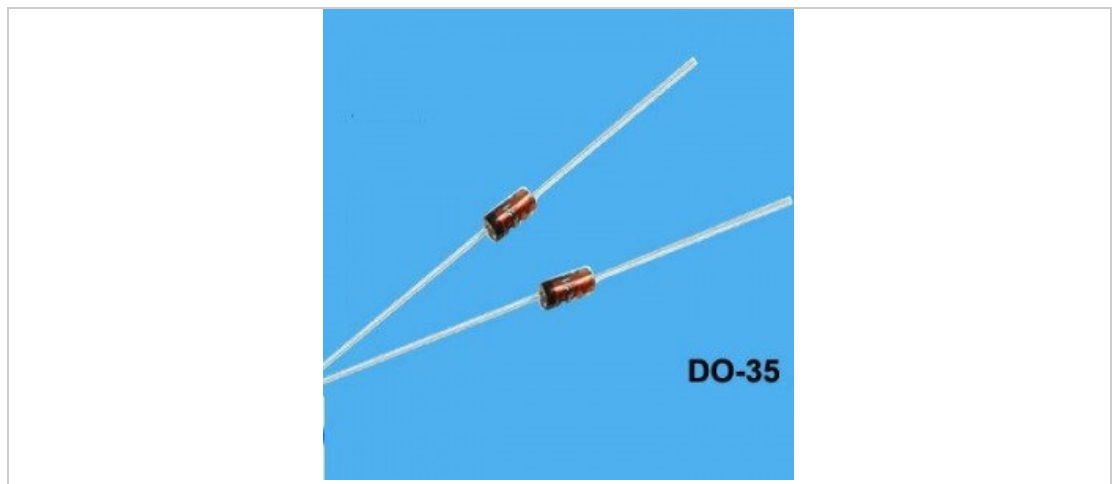




DB3 DB4 SILICON BIDIRECTIONAL DIACS DO-35



Specifications

DB3 DB4 SILICON BIDIRECTIONAL DIACS DO-35

Characteristics at $T_a = 25^\circ\text{C}$

Parameter		Symbol	Min.	Max.	Unit
Breakover Voltage	DB-3	$V_{(BR)1}$ and $V_{(BR)2}$	28	36	V
	DB-4		35	45	
Breakover Currents		$I_{(BR)1}$ and $I_{(BR)2}$	-	200	μA
Breakover Voltage Symmetry		$[V_{(BR)1}] - [V_{(BR)2}]$	-	3.8	V
Dynamic Breakover Voltage $\Delta I = [I_{BR} \text{ to } I_F = 10 \text{ mA}]$		$ \Delta V \pm $	5	-	V
Thermal Impedance Junction to Ambient Air		$R_{\theta JA}$	-	60	$^\circ\text{C/W}$